SILICON PLASTIC POWER TRANSISTOR
PNP TIP32C
3A 40W

Technical Data

…designed for use in general-purpose switching and amplifier applications.

- DC Current Gain - h_{FE} = 10- 50 @ IC = 3.0Adc
- Collector-Emitter Saturation Voltage – V_{CE} (sat) = 1.2Vdc (Max)@I_C=3Adc
- TO-220 Package
- Collector-Emitter Sustaining Voltage – $V_{CE\ O}$(sus) = 100Vdc (Min)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector- Emitter Voltage	V_{CEO}	100	Vdc
Collector – Base Voltage	V_{CB}	100	Vdc
Emitter Base Voltage	V_{EB}	5	Vdc
Collector Current – Continuos Peak	I_C	3 5	Adc
Base Current	I_B	1	Adc
Total Power Dissipation @ TC = 25°C Derate above 25°C	PD	40 0.32	Watts W/°C
Operating and Storage junction Temperature Range	Tj,Tstg	-65 to +150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max.	Unit
Thermal resistance junction to case	R_{thjc}	3.125	°C/W

ELECTRICAL CHARACTERISTICS :[Tc = 25 °C unless otherwise noted]

Characteristic	Symbol	Min	Typ	Max	Unit
*** OFF CHARACTERISTICS :**					
Collector–Emitter Sustaining Voltage(1) [Ic =30 mAdc, I_B = 0]	$V_{CEO(sus)}$	100			Vdc
Collector Cutoff Current [V_{CE} = 60 Vdc, I_B = 0]	I_{CE0}			0..3	mAdc
Collector Cutoff Current [V_{CE} =100 Vdc,V_{BE} = 0]	I_{CES}			200	✪Adc
Emitter Cutoff Current [V_{BE}=5.0 Vdc , Ic = 0]	I_{EBO}			1	mAdc
*** ON CHARACTERISTICS (1):**					
DC Current Gain [Ic = 1.0 Adc , V_{CE} = 4.0 Vdc] [Ic = 3Adc , V_{CE} = 4.0 Vdc]	h_{FE}	25 10		--- 50	
Collector-Emitter Saturation Voltage [Ic = 3Adc , I_B = 375mAdc)	$V_{CE(sat)}$			1.2	Vdc
Base-Emitter on Voltage [Ic =3.0 Adc , V_{CE}= 4.0. V_{DC}]	$V_{BE(on)}$			1.8	Vdc
DYNAMIC CHARACTERISTICS :					
Current Gain – Bandwidth Product [Ic=0.5Adc,V_{CE}=10Vdc,ftest=1.0 MHz]	f_T	3			MHz
Small-Signal Current Gain [I_C= 0.5 Adc, V_{CE}=10 Vdc, f=1kHz]	hfe	20			

· Indicates within JEDEC Registration Data.

· (1) Pulse Test : Pulse Width <300μs , Duty Cycle < 2.0%